

10/060,323

IN THE CLAIMS:

Please cancel Claims 1 and 10-17 without prejudice or disclaimer.

Please amend Claims 2,3,4,7 and 8, as follows:

1. (Cancelled)

2. (Currently Amended): A semiconductor device according to ~~claim 1~~ claim 4, wherein the carrier substrate is formed of ceramics.

3. (Currently Amended): A semiconductor device according to ~~claim 1~~ claim 4, further comprising conductive patterns that are formed on the carrier substrate and connected with the temperature sensing resistive element at a temperature sensing resistive element portion thereof, which is of a selected width.

4. (Currently Amended): A semiconductor device ~~according to claim 3~~, comprising:
a carrier substrate;
a temperature sensing resistive element deposited directly on the carrier substrate;
a semiconductor element mounting portion laid on the carrier substrate;
a semiconductor element mounted on the semiconductor element mounting portion; and
conductive patterns that are formed on the carrier substrate and connected with the
temperature sensing resistive element at a temperature sensing resistive element portion thereof,

10/060,323

which is of a selected width,

wherein each of the conductive patterns has a wire-bonding point, connected at a wire-bonding point portion of a selected width, that is electrically connected to an outside, and has a portion between the wire-bonding point portion and the temperature sensing resistive element portion, having a lower thermal conductivity than said wire-bonding point portion and said temperature sensing resistive element portion.

5. (Previously Presented): A semiconductor device according to claim 4, wherein the portion having the lower thermal conductivity is a portion directed in a path having bends.

6. (Previously Presented): A semiconductor device according to claim 4, wherein the portion having the lower thermal conductivity is of a width smaller than widths of said wire-bonding point portion and said temperature sensing resistive element portion.

7. (Currently Amended): A semiconductor device according to ~~claim 1~~ claim 4, wherein the temperature sensing resistive element contains at least one of Mn, Ni, Co, and Fe.

8. (Currently Amended): A semiconductor device according to ~~claim 1~~ claim 4, wherein the semiconductor element is a semiconductor laser.

10/060,323

9. (Original): A semiconductor device according to claim 8, wherein a heat sink is interposed between the semiconductor laser and the mounting portion.

10. (Cancelled)

11. (Cancelled)

12. (Cancelled)

13. (Cancelled)

14. (Cancelled)

15. (Cancelled)

16. (Cancelled)

17. (Cancelled)